De-Sheng Jiang

List of Publications by Year
in descending order

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26	353	933447	794594
papers	citations	10 h-index	19 g-index

26	26	26	414
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Deep levels induced optical memory effect in thin InGaN film. AIP Advances, 2018, 8, 085222.	1.3	1
2	Resistivity reduction of low temperature grown p-Al0.09Ga0.91N by suppressing the incorporation of carbon impurity. AIP Advances, 2018, 8, 085005.	1.3	2
3	Electroluminescence property improvement by adjusting quantum wellsâ€™ position relative to p-doped region in InGaN/GaN multiple-quantum-well light emitting diodes. AIP Advances, 2017, 7, 035103.	1.3	0
4	Fabrication of room temperature continuous-wave operation GaN-based ultraviolet laser diodes. Journal of Semiconductors, 2017, 38, 051001.	3.7	48
5	1.3 Î¼m single-photon emission from strain-coupled bilayer of InAs/GaAs quantum dots at the temperature up to 120â€‰K. Applied Physics Letters, 2017, 111, .	3.3	6
6	Different influences of u-InGaN upper waveguide on the performance of GaN-based blue and green laser diodes. Chinese Physics B, 2017, 26, 114203.	1.4	2
7	New design of upper waveguide with unintentionally doped InGaN layer for InGaN-based laser diode. Optics and Laser Technology, 2017, 97, 284-289.	4.6	7
8	Tuning exciton energy and fine-structure splitting in single InAs quantum dots by applying uniaxial stress. AIP Advances, 2016, 6, .	1.3	5
9	Different variation behaviors of resistivity for high-temperature-grown and low-temperature-grown p-GaN films. Chinese Physics B, 2016, 25, 027102.	1.4	7
10	The thickness design of unintentionally doped GaN interlayer matched with background doping level for InGaN-based laser diodes. AIP Advances, 2016, 6, 035124.	1.3	6
11	Influence of residual carbon impurities in i-GaN layer on the performance of GaN-based p-i-n photodetectors. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2016, 34, 011204.	1.2	4
12	Observation of negative differential resistance in GaN-based multiple-quantum-well light-emitting diodes. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2016, 34, 011206.	1.2	0
13	Investigation of breakdown mechanism during field emission process of AlN thin film microscopic cold cathode. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2016, 34, 012201.	1.2	1
14	Utilization of polarization-inverted AlInGaN or relatively thinner AlGaN electron blocking layer in InGaN-based blueâ€“violet laser diodes. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2015, 33, 011209.	1.2	8
15	Single-Photon Emission from GaAs Quantum Dots Embedded in Nanowires. Chinese Physics Letters, 2015, 32, 077804.	3.3	9
16	Coupling and single-photon purity of a quantum dot-cavity system studied using hydrostatic pressure. Journal of Applied Physics, 2015, 117, 014304.	2.5	6
17	In situ tuning biexciton antibinding-binding transition and fine-structure splitting through hydrostatic pressure in single InGaAs quantum dots. Europhysics Letters, 2014, 107, 27008.	2.0	13
18	Unintentionally doped semi-insulating GaN with a low dislocation density grown by metalorganic chemical vapor deposition. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2014, 32, 051207.	1.2	13

#	Article	IF	Citations
19	Performance comparison of front- and back-illuminated modes of the AlGaN-based p-i-n solar-blind ultraviolet photodetectors. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2014, 32, 031204.	1.2	9
20	The significant effect of the thickness of Ni film on the performance of the Ni/Au Ohmic contact to p-GaN. Journal of Applied Physics, 2014, 116, .	2.5	11
21	Investigation on the compensation effect of residual carbon impurities in low temperature grown Mg doped GaN films. Journal of Applied Physics, 2014, 115, 163704.	2.5	35
22	Effects of thin heavily Mg-doped GaN capping layer on ohmic contact formation of p-type GaN. Semiconductor Science and Technology, 2013, 28, 105020.	2.0	11
23	Design Considerations for GaN-Based Blue Laser Diodes With InGaN Upper Waveguide Layer. IEEE Journal of Selected Topics in Quantum Electronics, 2013, 19, 1500705-1500705.	2.9	16
24	Suppression of thermal degradation of InGaN/GaN quantum wells in green laser diode structures during the epitaxial growth. Applied Physics Letters, 2013, 103, .	3.3	68
25	Improvement of characteristics of InGaN-based laser diodes with undoped InGaN upper waveguide layer. Journal of Applied Physics, 2012, 112, .	2.5	25
26	Effects of edge dislocations and intentional Si doping on the electron mobility of n-type GaN films. Applied Physics Letters, 2006, 89, 112106.	3.3	40